

Oleg Komkov

List of Publications by Year in descending order

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times ranked

134
citing authors

#	ARTICLE	IF	CITATIONS
1	Photomodulation fourier transform infrared spectroscopy of semiconductor structures: Features of phase correction and application of method. Technical Physics Letters, 2013, 39, 1071-1073.	0.2	21
2	Temperature-dependent photoluminescence of InSb/InAs nanostructures with InSb thickness in the above-monolayer range. Journal Physics D: Applied Physics, 2016, 49, 285108.	1.3	21
3	Effect of external electric field on the probability of optical transitions in InGaAs/GaAs quantum wells. Semiconductors, 2006, 40, 592-597.	0.2	17
4	Metamorphic InAs(Sb)/InGaAs/InAlAs nanoheterostructures grown on GaAs for efficient mid-IR emitters. Progress in Crystal Growth and Characterization of Materials, 2019, 65, 20-35.	1.8	17
5	Molecular Beam Epitaxy of Layered Group III Metal Chalcogenides on GaAs(001) Substrates. Materials, 2020, 13, 3447.	1.3	16
6	InSb/InAs/InGa(Al)As/GaAs(001) metamorphic nanoheterostructures grown by MBE and emitting beyond 3 μm . Journal of Crystal Growth, 2017, 477, 97-99.	0.7	14
7	Determination of the free carrier concentration in ultra-pure GaAs epilayers by a photoreflectance technique. Technical Physics Letters, 2008, 34, 37-39.	0.2	13
8	Photoreflectance of indium antimonide. Physics of the Solid State, 2016, 58, 2394-2400.	0.2	13
9	Enhanced room-temperature 3.5 μm photoluminescence in stress-balanced metamorphic In(Sb,As)/In(Ga,Al)As/GaAs quantum wells. Applied Physics Express, 2017, 10, 121201.	1.1	13
10	Optical Properties of Epitaxial Al _x In _{1-x} Sb Alloy Layers. Semiconductors, 2011, 45, 1425-1429.	0.2	10
11	Radiative versus non-radiative recombination in high-efficiency mid-IR InSb/InAs/In(Ga,Al)As/GaAs metamorphic nanoheterostructures. Journal Physics D: Applied Physics, 2018, 51, 055106.	1.3	10
12	Excitonic effects and Franz-Keldysh oscillations in photoreflectance of ultrapure GaAs epilayers. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 842-846.	0.8	9
13	Determination of the thickness and spectral dependence of the refractive index of Al _x In _{1-x} Sb epitaxial layers from reflectance spectra. Semiconductors, 2013, 47, 292-297.	0.2	9
14	Metamorphic InAs/InGaAs/InAlAs quantum wells with submonolayer InSb insertions emitted in the mid-infrared spectral range. Technical Physics Letters, 2016, 42, 1038-1040.	0.2	9
15	Investigation of Built-in Electric Fields at the GaSe/GaAs Interface by Photoreflectance Spectroscopy. Semiconductors, 2020, 54, 1198-1204.	0.2	9
16	Evaluation of nitrogen incorporation into bulk 4H-SiC grown on seeds of different orientation from optical absorption spectra. Journal of Physics: Conference Series, 2016, 741, 012043.	0.3	8
17	Infrared photoreflectance of InSb-based two-dimensional nanostructures. Journal of the Optical Society of America B: Optical Physics, 2019, 36, 910.	0.9	8
18	Photoreflectance characterization of gallium arsenide. Russian Microelectronics, 2012, 41, 508-510.	0.1	7

#	ARTICLE	IF	CITATIONS
19	Tuning the structural and optical properties of GeSiSn/Si multiple quantum wells and GeSn nanostructures using annealing and a faceted surface as a substrate. Applied Surface Science, 2022, 593, 153421.	3.1	7
20	Effect of electric field on the probability of optical transitions in InGaAs/GaAs quantum wells observed by photo- and electroreflectance methods. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 1270-1274.	0.8	6
21	Molecular Beam Epitaxy Growth and Optical Characterization of Al _x In _{1-x} Sb/GaAs Heterostructures. , 2011, , .		5
22	Photoreflectance of GaAs structures with a Mn ²⁺ -doped layer. Technical Physics Letters, 2013, 39, 1008-1011.	0.2	5
23	Determination of InSb/AlInSb quantum well energy spectrum. Journal of Physics: Conference Series, 2014, 541, 012085.	0.3	5
24	Investigation of GaAs/AlGaAs superlattice by photoreflectance method. Journal of Physics: Conference Series, 2018, 1038, 012124.	0.3	4
25	Peculiarities of the energy spectrum of InSb/InAs/InGaAs/InAlAs/GaAs nanoheterostructures revealed by room temperature photomodulation FTIR spectroscopy. Japanese Journal of Applied Physics, 2019, 58, 050923.	0.8	4
26	Effect of Strongly Mismatched GaAs and InAs Inserts in a InAlAs Buffer Layer on the Structural and Optical Properties of Metamorphic InAs(Sb)/InGaAs/InAlAs/GaAs Quantum-Confined Heterostructures. JETP Letters, 2019, 109, 377-381.	0.4	4
27	Effect of design and stress relaxation on structural, electronic, and luminescence properties of metamorphic InAs(Sb)/In(Ga,Al)As/GaAs mid-IR emitters with a superlattice waveguide. Journal of Applied Physics, 2020, 127, 125706.	1.1	4
28	Epitaxial growth of peculiar GeSn and SiSn nanostructures using a Sn island array as a seed. Applied Surface Science, 2021, 553, 149572.	3.1	4
29	Determination of the indium arsenide autoepitaxial layers'™ thickness by Fourier-Transform Infrared Spectroscopy. Russian Microelectronics, 2015, 44, 575-578.	0.1	2
30	Contactless characterization of manganese and carbon delta-layers in gallium arsenide. Semiconductors, 2017, 51, 1420-1426.	0.2	2
31	FTIR photoreflectance of narrow-gap heterostructures based on Al _x In _{1-x} Sb alloys. Journal of Physics: Conference Series, 2017, 917, 062025.	0.3	2
32	Contactless Measurement of Electron Concentration in Undoped Homoepitaxial InSb Layers. Journal of Communications Technology and Electronics, 2018, 63, 289-291.	0.2	2
33	Infrared photoluminescence spectra measurements using boxcar integrator in the active baseline subtraction mode. Journal of Physics: Conference Series, 2019, 1400, 066035.	0.3	2
34	Effect of the Crystallographic Orientation of GaSb Films on Their Structural Properties during MBE Heteroepitaxy on Vicinal Si(001) Substrates. Semiconductors, 2020, 54, 1548-1554.	0.2	2
35	Study of structural and optical properties of a dual-band material based on tin oxides and GeSiSn compounds. Applied Surface Science, 2022, 573, 151615.	3.1	2
36	Effect of surface morphology on macroscale and microscale optical properties of layered InSe grown by molecular beam epitaxy. Journal of the Optical Society of America B: Optical Physics, 2021, 38, 2579.	0.9	1

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37	Infrared Photoreflectance of III-V Semiconductor Materials (Review). Physics of the Solid State, 2021, 63, 1181-1204.	0.2	1
38	Photoluminescence of undoped InAs autoepitaxial layers. Journal of Physics: Conference Series, 2015, 643, 012051.	0.3	0
39	Phase-sensitive photoreflectance investigation of InGaAs/GaAs quantum well structures. , 2016, , .		0
40	Interpretation of photoluminescence spectra of metamorphic InAlAs/GaAs heterostructures. Journal of Physics: Conference Series, 2019, 1410, 012167.	0.3	0
41	Measurement of Infrared Photoluminescence Spectra by Gated Integration with Active Baseline Subtraction. Optics and Spectroscopy (English Translation of Optika i Spektroskopiya), 2020, 128, 131-136.	0.2	0
42	10.1007/s11455-008-1011-0. , 2010, 34, 37.		0
43	Investigation of energy transitions in MoS ₂ by photoreflectance spectroscopy method. Journal of Physics: Conference Series, 2020, 1695, 012111.	0.3	0
44	Structural and Optical Properties of a Hybrid Material Based on Tin Oxides and Multilayer Periodic Structures with Pseudomorphic GeSiSn Layers. Russian Physics Journal, 0, , 1.	0.2	0
45	Investigation of infrared photoluminescence spectra of Ge _{1-x-y} Si _x Sn _y /Si nanostructures. Journal of Physics: Conference Series, 2022, 2227, 012009.	0.3	0
46	Characterization of In(Ga,Al)As/GaAs metamorphic heterostructures for mid-IR emitters by FTIR photoreflectance spectroscopy. Journal of Physics: Conference Series, 2021, 2086, 012140.	0.3	0